

Taiwan Semiconductor

# **N-Channel Power MOSFET**

100V, 6.5A, 95mΩ

#### **FEATURES**

- · Fast switching
- Pb-free plating
- RoHS compliant
- Halogen-free mold compound

#### **APPLICATION**

- Networking
- Load Switch
- Lighting

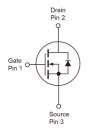
KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V <sub>DS</sub>	$V_{DS}$		V	
<b>5</b>	$V_{GS} = 10V$	95		
$R_{DS(on)}$ (max)	V <sub>GS</sub> = 4.5V	110	mΩ	
$Q_{g}$		9.3	nC	











Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	100	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	I <sub>D</sub>	6.5	^	
	$T_C = 100$ °C		4.1	<b>A</b>	
Pulsed Drain Current (Note 2)	·	I <sub>DM</sub>	26	Α	
Total Power Dissipation @ $T_C = 25$ °C		$P_{DTOT}$	9	W	
Operating Junction and Storage Tempe	rature Range	$T_J,T_STG$	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R <sub>eJC</sub>	14	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62	°C/W	

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JC}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB in still air

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	100			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.6	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
	$V_{GS} = 10V, I_D = 5A$	_		80	95	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 3A$	$R_{DS(on)}$		85	110	
Dynamic (Note 4)						
Total Gate Charge		Qg		9.3		
Gate-Source Charge	$V_{DS} = 48V, I_D = 5A,$ $V_{GS} = 10V$	$Q_{gs}$		2.1		nC
Gate-Drain Charge		$Q_{gd}$		1.8		
Input Capacitance		C <sub>iss</sub>		1480		
Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V,$	C <sub>oss</sub>		480		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		35		
Gate Resistance	f = 1MHz, open drain	$R_{g}$		1.3		Ω
Switching (Note 5)						
Turn-On Delay Time		t <sub>d(on)</sub>		2.9		
Turn-On Rise Time	$\begin{aligned} &V_{DD} = 30V, \\ &R_{GEN} = 3.3\Omega, \\ &I_{D} = 1A, \ V_{GS} = 10V, \end{aligned}$	t <sub>r</sub>		9.5		
Turn-Off Delay Time		t <sub>d(off)</sub>		18.4		ns
Turn-Off Fall Time		t <sub>f</sub>		5.3		
Source-Drain Diode (Note 3)						
Forward On Voltage	$I_S = 3.3A, V_{GS} = 0V$	V <sub>SD</sub>			1	V
Continuous Drain-Source Diode	•	Is			6.5	Α
Pulse Drain-Source Diode		I <sub>SM</sub>			26	Α

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### Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. Pulse test: PW  $\leq$  300 $\mu$ s, duty cycle  $\leq$  2%
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.



## **ORDERING INFORMATION**

ORDERING CODE	PACKAGE	PACKING
TSM950N10CW RPG	SOT-223	2,500pcs / 13" Reel

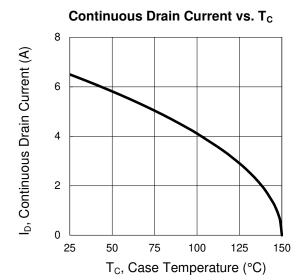
### Note:

- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC 1.
- Halogen-free according to IEC 61249-2-21 definition



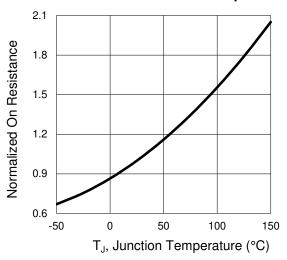
### **CHARACTERISTICS CURVES**

(T<sub>C</sub> = 25°C unless otherwise noted)

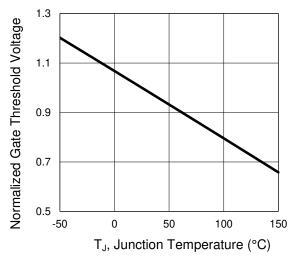


# **Gate Charge** 10 V<sub>GS</sub>, Gate to Source Voltage (V) ID=5A VDS=48V 8 6 4 2 0 2 10 0 Qg, Gate Charge (nC)

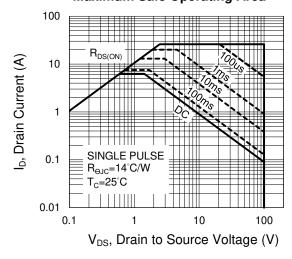




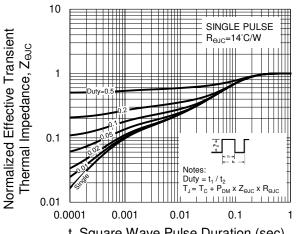




## **Maximum Safe Operating Area**



## **Normalized Thermal Transient Impedance Curve**



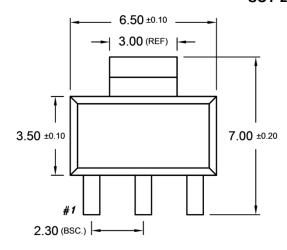
t, Square Wave Pulse Duration (sec)

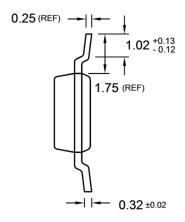


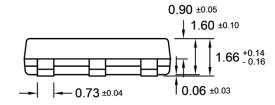
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## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

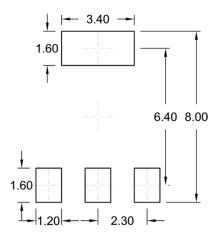
**SOT-223** 







## **SUGGESTED PAD LAYOUT** (Unit: Millimeters)



### **MARKING DIAGRAM**



Y = Year Code

**M** = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

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 $\mathbf{L} = \text{Lot Code } (1 \sim 9, A \sim Z)$ 



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